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Kind regards,

Team Nexperia

**PNP/PNP** resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

Rev. 02 — 1 September 2009

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

PNP/PNP resistor-equipped transistors

Table 1.	Product	overview
		0.0.0.0.0

Type number	Type number Package		NPN/PNP	NPN/NPN	
	NXP	JEITA	complement	complement	
PEMB19	SOT666	-	PEMD19	PEMH19	
PUMB19	SOT363	SC-88	PUMD19	PUMH19	

#### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

#### **1.3 Applications**

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

#### 1.4 Quick reference data

#### Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-50	V
lo	output current (DC)		-	-	-100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ



*006aaa268* 

#### **PNP/PNP** resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

# 2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

# 3. Ordering information

Table 4.	Ordering information	
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Type number	Package				
	Name	Description	Version		
PEMB19	-	plastic surface mounted package; 6 leads	SOT666		
PUMB19	SC-88	plastic surface mounted package; 6 leads	SOT363		

## 4. Marking

Table 5. Marking codes	
Type number	Marking code <sup>[1]</sup>
PEMB19	6D
PUMB19	T3*

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

#### **PNP/PNP** resistor-equipped transistors; $R1 = 22 k\Omega$ , R2 = open

## 5. Limiting values

Symbol	Parameter	Conditions	Min	Мах	Unit
Per transis	stor				
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-5	V
lo	output current (DC)		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		<u>[1] [2]</u> _	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> _	300	mW
	SOT666		<u>[1] [2]</u> _	300	mW

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

## 6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per trans	istor					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		<u>[1] [2]</u> _	-	625	K/W
Per devic	e					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1] [2] _	-	416	K/W

[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

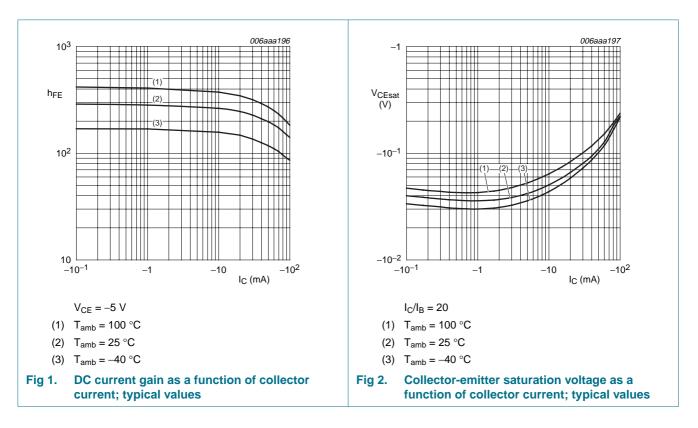
PNP/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = open

# 7. Characteristics

#### Table 8. Characteristics

T<sub>amb</sub> = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I <sub>CEO</sub> collector-	collector-emitter	$V_{CE} = -30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	-1	μA
	cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_C = -1 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = -10$ mA; $I_{B} = -0.5$ mA	-	-	-150	mV
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A};$ f = 1 MHz	-	-	3	pF

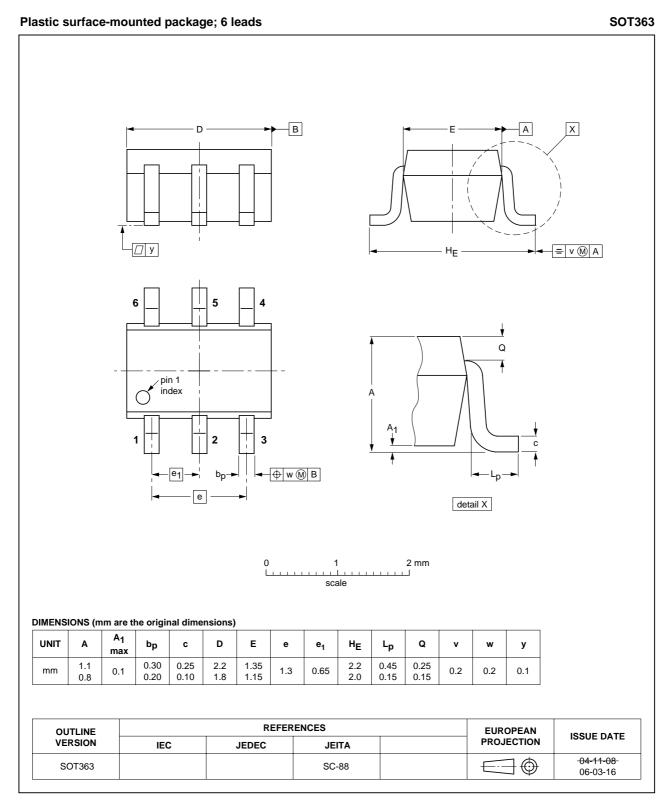


#### **NXP Semiconductors**

PEMB19; PUMB19

PNP/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

## 8. Package outline



#### Fig 3. Package outline SOT363 (SC-88)

**PNP/PNP** resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

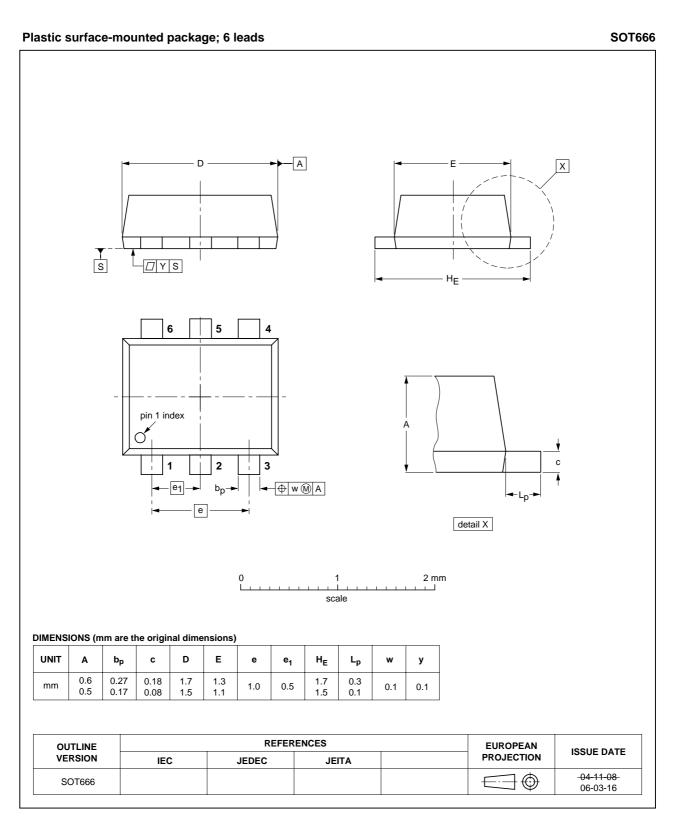


Fig 4. Package outline SOT666

PEMB19\_PUMB19\_2 Product data sheet **PNP/PNP** resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

# 9. Packing information

#### Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing q	juantity	
			3000	4000	10000
PEMB19	SOT666	4 mm pitch, 8 mm tape and reel;	-	-115	-
PUMB19	SOT363	4 mm pitch, 8 mm tape and reel; T1	<sup>[2]</sup> -115	-	-135
PUMB19	SOT363	4 mm pitch, 8 mm tape and reel; T2	<u>3</u> -125	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

PNP/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = open

# **10. Revision history**

Table 10. Revision histo	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMB19_PUMB19_2	20090901	Product data sheet	-	PEMB19_PUMB19_1
Modifications:		t was changed to reflect the egal definitions and discla		
	<ul> <li>Figure 3 "Packa</li> </ul>	age outline SOT363 (SC-8	88)": updated	
	Figure 4 "Packa	age outline SOT666": upd	ated	
PEMB19_PUMB19_1	20050202	Product data sheet	-	-

**PNP/PNP** resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

# **11. Legal information**

#### 11.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PEMB19\_PUMB19\_2
Product data sheet

#### **NXP Semiconductors**

# PEMB19; PUMB19

**PNP/PNP** resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

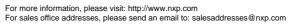
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